

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A thin film transistor, comprising:

a gate electrode having a gate insulation film;

a channel regionsregion that extend~~extends~~ through the gate insulation film in the gate electrode; and

source drain regions connected to said channel regionsregion that are formed against a semiconductor film that is formed on the surface of an insulation substrate, wherein a recombination e~~center~~center which captures~~captures~~ carriers are~~is~~ formed in said channel regionsregion by part of a crystal semiconductor film~~film~~ having a relatively low degree of crystallization among~~in~~ crystal semiconductor film~~film~~ that form~~forms~~ said channel regionsregion.

2. (Currently Amended) The thin film transistor of Claim 1, wherein said recombination e~~center~~center are~~is~~ concentrated adjacent to said drain regions within said channel regionsregion.

3. (Currently Amended) The thin film transistor of Claim 2, wherein said recombination e~~center~~center are~~is~~ concentrated in a region, among channel regions, whose distance from the drain regions is equivalent to 1/3 to 1/10 of a channel length.

4. (Currently Amended) The thin film transistor according to Claim 1, wherein a regionsregion, among~~in~~ said channel regionsregion, in which said recombination e~~center~~center are~~is~~ concentrated have~~has~~ different film thickness compared to other regionsregion.

5. (Currently Amended) The thin film transistor according to Claim 1, wherein a regionsregion, among~~in~~ said channel regionsregion, in which said recombination

~~centerscenter areis~~ concentrated ~~havehas~~ different surface positions compared to other regions.

6. (Currently Amended) The thin film transistor of Claim 5, wherein the ~~regionsregion, amongin~~ said channel ~~regionsregion~~, in which said recombination ~~centerscenter areis~~ concentrated ~~havehas~~ different surface height positions compared to other regions due to a different thickness of the semiconductor ~~filmsfilm~~ forming said channel ~~regionsregion~~.

7. (Currently Amended) The thin film transistor of Claim 5, wherein the ~~regionsregion, amongin~~ said channel ~~regionsregion~~, in which said recombination ~~centerscenter areis~~ concentrated ~~havehas~~ different surface height positions compared to other regions due to the formation of at least one of indented sections and bulged sections in a lower layer of the semiconductor films forming said channel regions.

8. (Withdrawn) A method for manufacturing a thin film transistor comprising a gate electrode having a gate insulation film, channel regions that extend through a gate insulation film in the gate electrode, and source drain regions connected to said channel regions that are formed against a semiconductor film being formed on a surface of an insulation substrate, wherein a section having a relatively low degree of crystallization is formed within a predetermined region of said semiconductor films by applying laser annealing to said semiconductor films after forming the semiconductor films that form said channel regions.

9. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 8, wherein a section with a relatively low degree of crystallization is formed in the predetermined regions of said semiconductor film by applying said laser annealing to said semiconductor film after forming the semiconductor films with partially different film thickness as semiconductor films that form said channel regions.

10. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 8, wherein a section with a relatively low degree of crystallization is formed in the predetermined regions to said semiconductor film by applying said laser annealing for said semiconductor film after forming the semiconductor films with different surface height positions as semiconductor films that form said channel regions.

11. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 10, wherein the thickness of said semiconductor film is made to be different partially in forming said semiconductor film with different surface height positions.

12. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 11, wherein at least one of an indented section and a bulging section is formed beforehand in a lower layer of said semiconductor films in forming said semiconductor films with different surface height positions.

13. (Currently Amended) The thin film transistor according to Claim 2, wherein ~~the regions~~^a region, ~~among~~ⁱⁿ said channel ~~regions~~^{region}, in which said recombination ~~centers~~^{center} ~~are~~^{is} concentrated have different film thickness compared to other regions.

14. (Currently Amended) The thin film transistor according to Claim 3, wherein ~~the regions~~^a region, ~~among~~ⁱⁿ said channel ~~regions~~^{region}, in which said recombination ~~centers~~^{center} ~~are~~^{is} concentrated ~~have~~^{has} different film thickness compared to other regions.

15. (Currently Amended) The thin film transistor according to Claim 2, wherein ~~the regions~~^a region, ~~among~~ⁱⁿ said channel ~~regions~~^{region}, in which said recombination ~~centers~~^{center} ~~are~~^{is} concentrated ~~have~~^{has} different surface positions compared to other regions.

16. (Currently Amended) The thin film transistor according to Claim 3, wherein ~~the regions~~^a region, ~~among~~ⁱⁿ said channel ~~regions~~^{region}, in which said recombination ~~centers~~^{center} ~~are~~^{is} concentrated have different surface positions compared to other regions.

17. (Currently Amended) A display device having a thin film transistor, the thin film transistor comprising:

a gate electrode having a gate insulation film;

a channel regionsregion that extends through the gate insulation film in the gate electrode; and

source drain regions connected to said channel regions that are formed against a semiconductor film that is formed on the surface of an insulation substrate, wherein a recombination centerscenter which capture carriers are is formed in said channel regionsregion by part of crystal semiconductor films having a relatively low degree of crystallization among crystal semiconductor films that form said channel regionsregion.

18. (Withdrawn) A method for manufacturing a display device having a thin-film transistor, the thin-film transistor comprising a:

gate electrode having a gate insulation film, channel regions that extend through a gate insulation film in the gate electrode, and source drain regions connected to said channel regions that are formed against a semiconductor film being formed on a surface of an insulation substrate, wherein a section having a relatively low degree of crystallization is formed within a predetermined region of said semiconductor films by applying laser annealing to said semiconductor films after forming the semiconductor films that form said channel regions.

19. (Currently Amended) A thin film transistor, comprising:

a channel region facing a gate electrode, the channel region having a partially distorted portion distorted in a thickness direction of the channel region;

source and drain regions connection to the channel region in a semiconductor film in contact with a surface of an insulating substrate;

a gate insulating film formed at least over the channel, and extend through the
source, and drain regions; and

a recombination center formed around the partially distorted portion, the
recombination center having a relatively low degree of crystallization among crystal
semiconductor films forming the channel region.